DACO SEMICONDUCTOR CO., LTD.

MBRQ200200CT(R)

SCHOTTKY DIODE MODULE TYPE 200A

Features

High Surge Capability

Type 200V V_{RRM}

TWIN TOWER Q

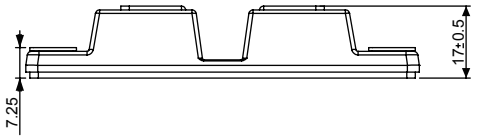
Maximum Ratings

Operating Temperature: -55℃ to +150℃

Storage Temperature: -55℃ to +150℃

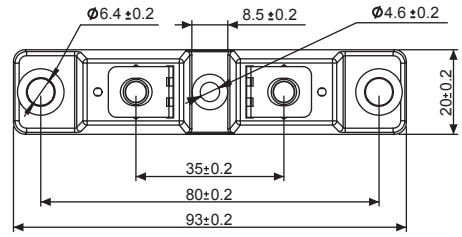
Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBRQ200200CT(R)	200V	140V	200V

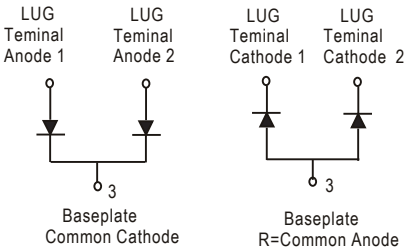
Dimensions in mm (1 mm = 0.0394")



Electrical Characteristics @ 25℃ Unless Otherwise Specified

Average Forward Current (Per pkg)	$I_{F(AV)}$	200A	TC=125℃
Peak Forward Surge Current (Per leg)	I_{FSM}	1500A	8.3ms , half sine
Maximum Instantaneous Forward Voltage (Per leg)	V_F	0.92V	I_{FM}=100A;TJ=25℃
Maximum Instantaneous Reverse Current At Rated DC Blocking Voltage (Per leg)	I_R	3mA 10mA 50mA	TJ= 25℃ TJ =100℃ TJ =150℃
Maximum Thermal Resistance Junction To Case (Per leg)	$R_{\theta jc}$	0.40℃/W	
Mounting torque		3 ± 0.5Nm 3 ± 0.5Nm	To heatsink To terminals





NOTE :

(1) Pulse Test: Pulse Width 300 μ sec. Duty Cycle < 2%

Figure.1 - Typical Forward Characteristics

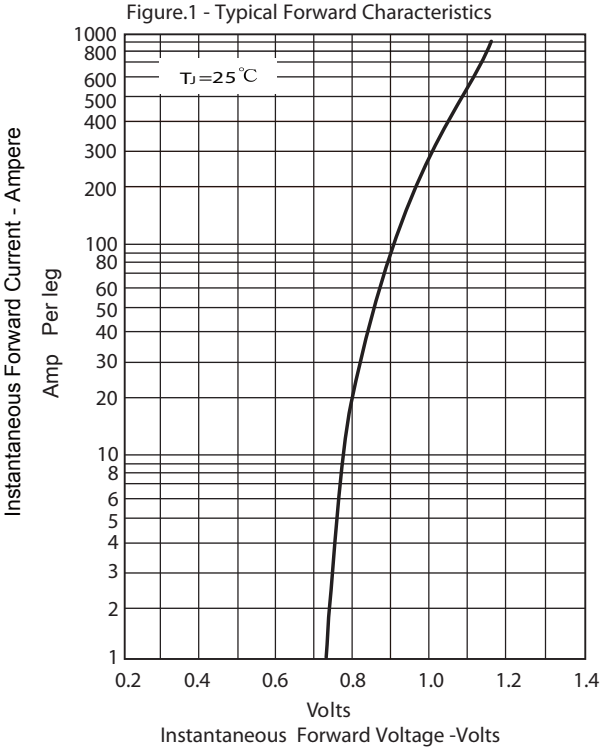
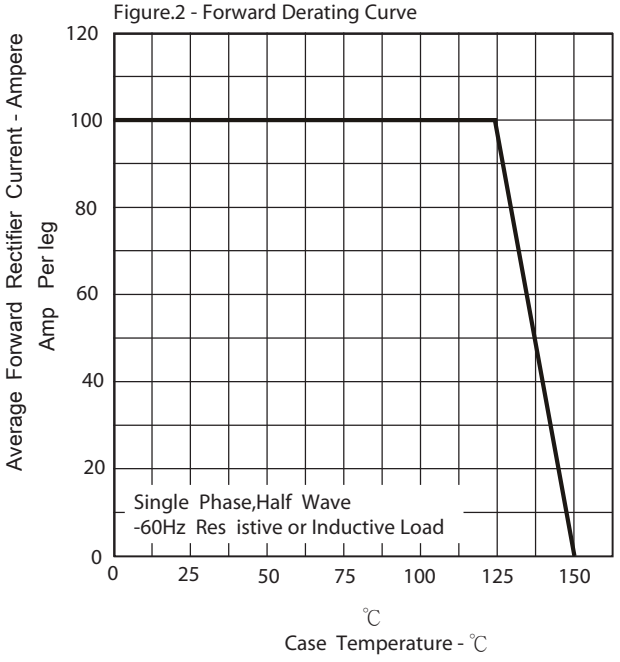


Figure.2 - Forward Derating Curve



Figupre.3 - Peak Forward Surge Current

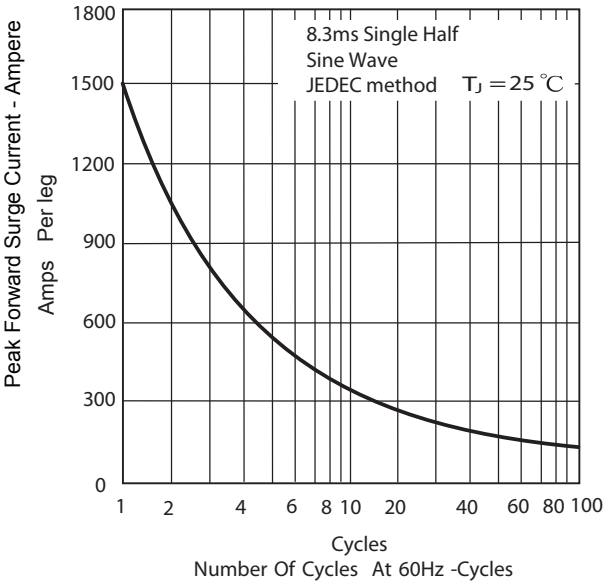


Figure.4 - Typical Reverse Characteristics